

**2SB1205**

Strobe High-Current Switching Applications

Applications

- Strobe, voltage regulators, relay drivers, lamp drivers.

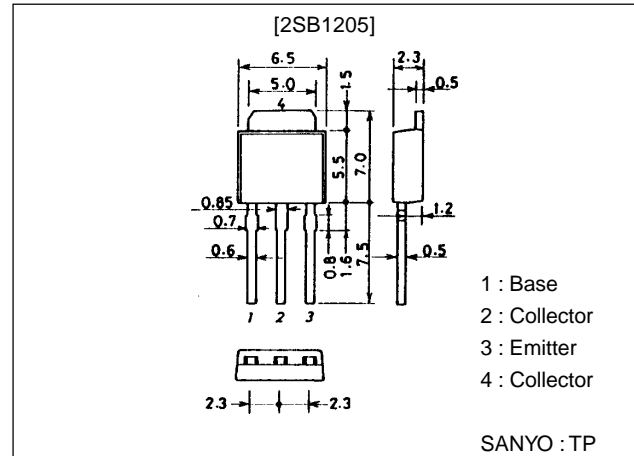
Features

- Adoption of FBET, MBIT processes.
- Low saturation voltage.
- Fast switching speed.
- Large current capacity.
- Small and slim package making it easy to make 2SB1205-applied sets smaller.

Package Dimensions

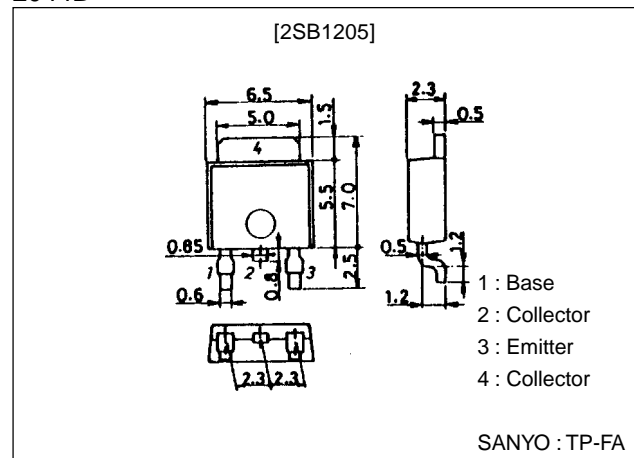
unit:mm

2045B



unit:mm

2044B



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2SB1205

Specifications

Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V_{CB0}		-25	V
Collector-to-Emitter Voltage	V_{CEO}		-20	V
Emitter-to-Base Voltage	V_{EBO}		-5	V
Collector Current	I_C		-5	A
Collector Current (Pulse)	I_{CP}		-8	A
Base Current	I_B		-0.5	A
Collector Dissipation	P_C		1	W
		$T_c=25^\circ\text{C}$	10	W
Junction Temperature	T_J		150	$^\circ\text{C}$
Storage Temperature	T_{stg}		-55 to +150	$^\circ\text{C}$

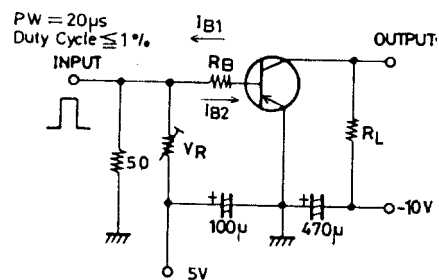
Electrical Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I_{CBO}	$V_{CB}=-20\text{V}, I_E=0$			-500	nA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=-4\text{V}, I_C=0$			-500	nA
DC Current Gain	h_{FE1}	$V_{CE}=-2\text{V}, I_C=500\text{mA}$	100*		400*	
	h_{FE2}	$V_{CE}=-2\text{V}, I_C=-4\text{A}$	60			
Gain-Bandwidth Product	f_T	$V_{CE}=-5\text{V}, I_C=-200\text{mA}$		320		MHz
Output Capacitance	C_{ob}	$V_{CE}=-10\text{V}, f=1\text{MHz}$		60		pF
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-3\text{A}, I_B=-60\text{mA}$		-250	-500	mV
Base-to-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=-3\text{A}, I_B=-60\text{mA}$		-1.0	-1.3	V
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=-10\mu\text{A}, I_E=0$	-25			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=-1\text{mA}, R_{BE}=\infty$	-20			V
Emitter-to-Base Breakdown Voltage	$V_{(BE)EBO}$	$I_E=-10\mu\text{A}, I_C=0$	-5			V
Turn-ON Time	t_{on}	See specified Test Circuit		40		ns
Storage Time	t_{stg}	See specified Test Circuit		200		ns
Fall Time	t_f	See specified Test Circuit		10		ns

* : The 2SB1205 is classified by 500mA h_{FE} as follows :

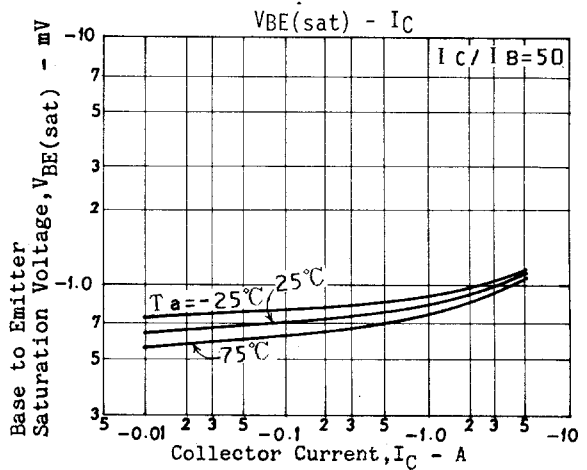
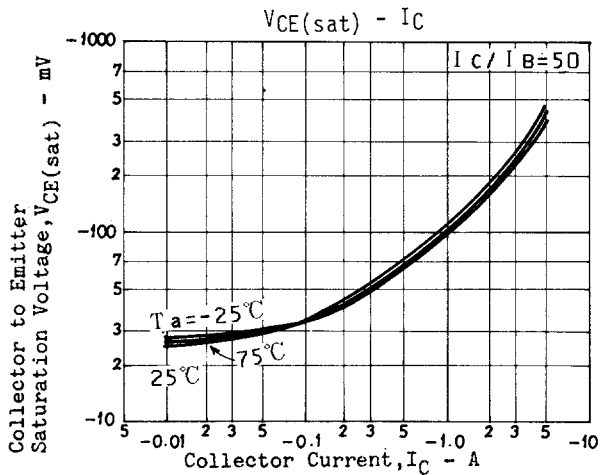
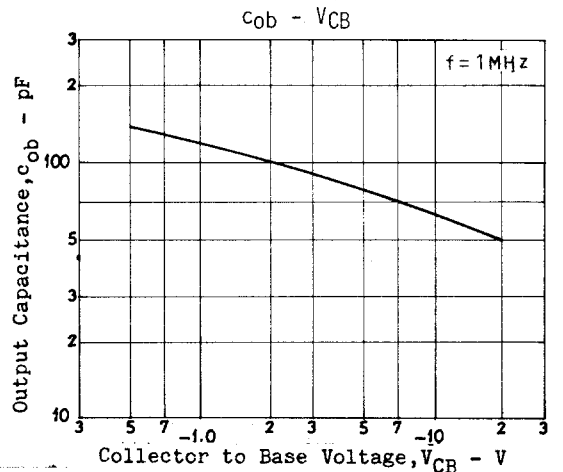
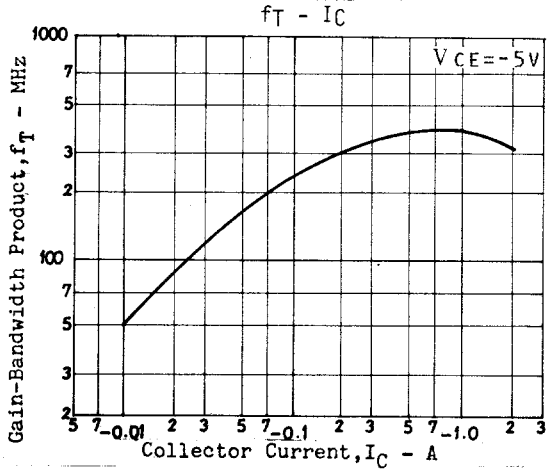
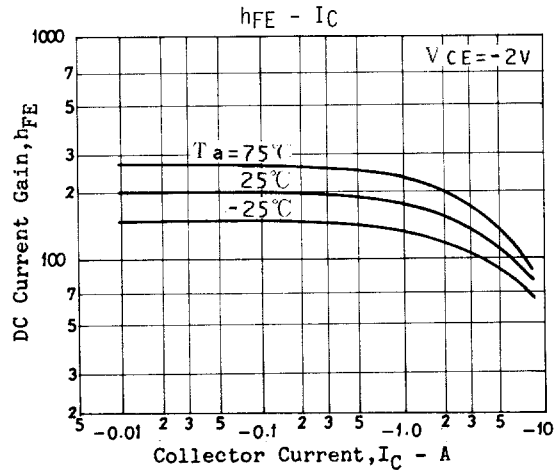
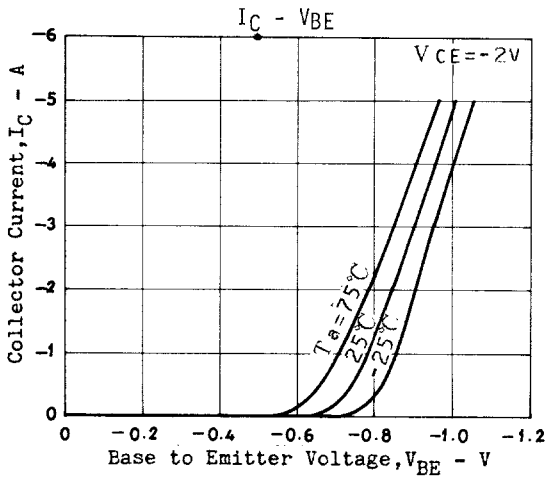
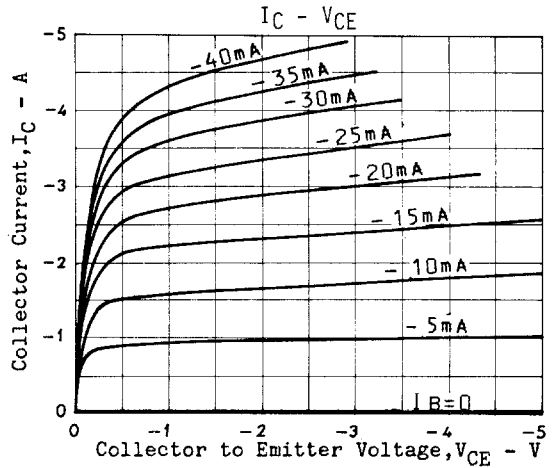
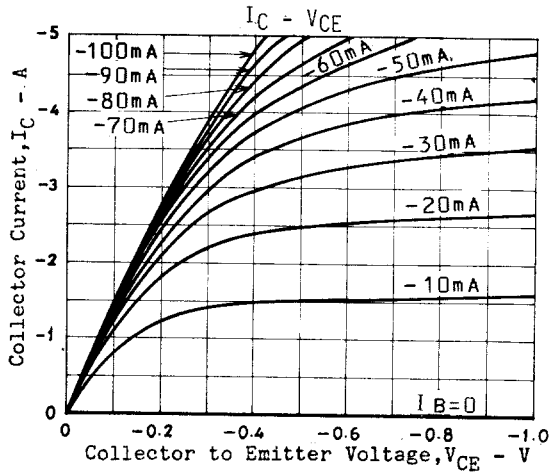
100 R 200	140 S 280	200 T 400
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Switching Time Test Circuit

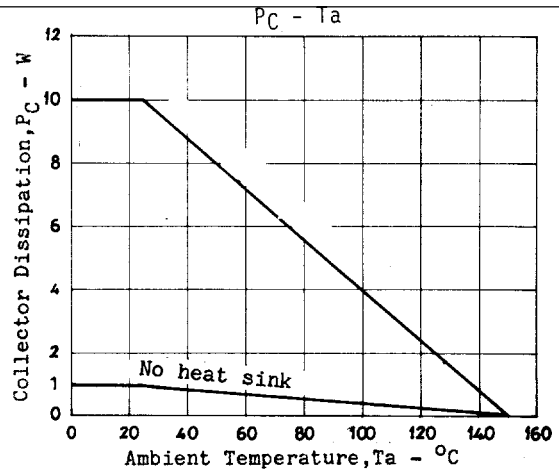
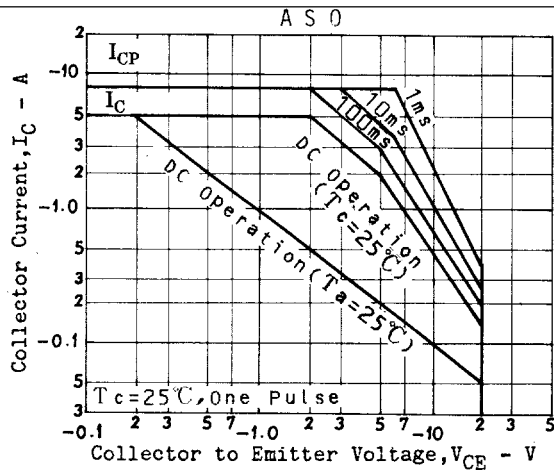


$I_C = -10 \text{ I}_B1 = 10 \text{ I}_B2 = -2 \text{ A}$
 Unit (resistance : Ω , capacitance : F)

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